

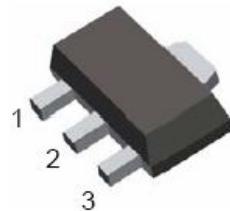
SOT-89 場效應晶體管(SOT-89 Field Effect Transistors)

SOT-89

1.Gate

2.Drain

3.Source



N-Channel Enhancement-Mode MOS FETs

N 沟道增强型 MOS 场效应管

■MAXIMUM RATINGS 最大額定值

Characteristic 特性參數	Symbol 符號	Max 最大值	Unit 單位
Drain-Source Voltage 漏極 - 源極電壓	BV _{DSS}	16	V
Gate- Source Voltage 柵極 - 源極電壓	V _{GS}	±16	V
Drain Current (continuous) 漏極電流 - 連續	I _D	3	A
Drain Current (pulsed) 漏極電流 - 脉沖	I _{DM}	6	A
Total Device Dissipation 總耗散功率 TA=25°C 環境溫度為 25°C	P _D	2	W
Channel Temperature 溝道溫度	T _{ch}	150	°C
Storage Temperature 儲存溫度	T _{stg}	-55to+150	°C

■DEVICE MARKING 打標

GM3066=NG**



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GM3066

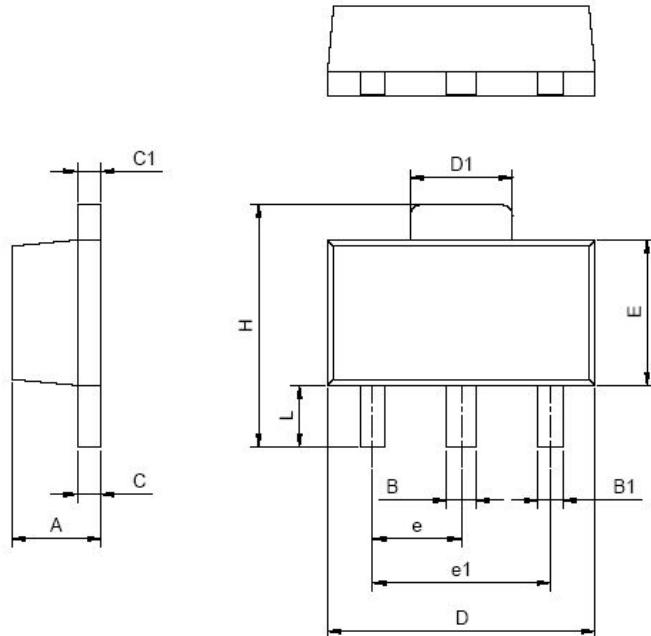
ELECTRICAL CHARACTERISTICS 電特性

(T_A=25°C unless otherwise noted 如無特殊說明，溫度為 25°C)

Characteristic 特性參數	Symbol 符號	Min 最小值	Typ 典型值	Max 最大值	Unit 單位
Drain-Source Breakdown Voltage 漏極-源極擊穿電壓(I _D = 250uA, V _{GS} =0V)	BVDSS	16	—	—	V
Gate Threshold Voltage 柵極開啓電壓(I _D = 1mA, V _{GS} = V _{DS})	V _{GS(th)}	0.8	—	1.6	V
Zero Gate Voltage Drain Current 零柵壓漏極電流(V _{GS} =0V, V _{DS} = 16V)	I _{DSS}	—	—	1	uA
Gate Body Leakage 柵極漏電流(V _{GS} =±16V, V _{DS} =0V)	I _{GSS}	—	—	±1	uA
Forward Transfer Admittance 正向傳輸導納(V _{DS} =3V, I _D =1A)	Y _{fs}	0.4	3	—	S
Static Drain-Source On-State Resistance 静态漏源導通電阻(I _D =1.5A, V _{GS} =4V) (I _D =1A, V _{GS} =2.5V)	R _{DS(ON)}	—	—	300 500	mΩ
Input Capacitance 輸入電容 (V _{GS} =0V, V _{DS} = 3V, f=1MHz)	C _{ISS}	—	240	—	pF
Common Source Output Capacitance 共源輸出電容(V _{GS} =0V, V _{DS} = 3V, f=1MHz)	C _{OSS}	—	100	—	pF
Turn-ON Time 开启時間 (V _{DS} = 3V, I _D = 1.5A, R _{GEN} =10Ω)	t _(on)	—	140	—	ns
Turn-OFF Time 关斷時間 (V _{DS} = 3V, I _D =1.5A, R _{GEN} =10Ω)	t _(off)	—	120	—	ns

Pulse Width≤300 μ s; Duty Cycle≤2.0%

■外形尺寸(DIMENSION)



Symbol	Inches		Millimeters		Notes
	Min.	Max.	Min.	Max.	
A	-	-	1.4	1.6	
B	-	-	.44	.56	
B1	-	-	.36	.48	
C	-	-	.35	.44	
C1	-	-	.35	.44	
D	-	-	4.4	4.6	
D1	-	-	1.62	1.83	
E	-	-	2.29	2.6	
e	-	-	1.42	1.57	
e1	-	-	2.92	3.07	
H	-	-	3.94	4.25	
L	-	-	0.89	1.2	